

UHF-Band Avionics Transistor

The high power pulsed avionics transistor part number IB0607S1000 is designed for UHF-Band avionics systems operating at 653 to 687 MHz. While operating in class C mode under 20us pulse conditions at $V_{CC}=50V$, this common base device supplies a minimum of 1000 watts of peak pulse power. It utilizes a low loss internal input impedance matching structure to yield maximum device gain and to ease the implementation of external matching circuitry. The new generation bipolar transistor geometry utilizes a gold metallization system to achieve maximum reliability. Emitter ballast resistance is incorporated on the active cell for optimum thermal distribution and maximum reliability. All devices are 100% screened for large signal RF parameters.

Silicon Bipolar

- Ultra-high f_T

Class C Operation

- High Efficiency

Common Base Configuration

- Single Power Supply

Gold Metal

- Maximum Reliability

Emitter Ballasting

- Optimum Thermal Distribution

Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

BeO Package

- Unmatched Thermal Reliability

RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed
- Micro-strip structure on soft pc board with dielectric constant 10.2

PRELIMINARY DATA

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Device	Freq (MHz)	V_{CC} (V)	P_{IN} (W)	IRL (dB)	P_{OUT} (W)	G_P (dB)	I_c (A)	η_c (%)	Droop (dB)
50028465-1	653	50	117.8	16.4	1000	9.29	36.30	55.1	0.05
	670	50	92.95	18	1000	10.32	31.25	64.0	0.10
	687	50	85.79	18	1000	10.67	30.00	66.7	0.08

Pulse Format : PW=20us, DF=2%

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	75	V	--
BD	Emitter-Base Voltage	V_{EBO}	--	2	V	--
BD	Storage Temperature Range	T_{STG}	-60	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-60	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.039	°C/W	$P_{OUT}=1000W, P_{IN}=126W, N_C=50\%, V_{CC}=50V, PW=20us, DF=2\%, T_F=30\pm 5^\circ C$
BD	MTTF	MTTF	8.60E14	--	Hrs	$P_{OUT}=1000W, P_{IN}=126W, N_C=50\%, V_{CC}=50V, PW=20us, DF=2\%, T_F=30\pm 5^\circ C$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	BV_{CES}	75	--	V	$I_C = 50mA, V_{BE} = 0V, T_F = 25\pm 5^\circ C.$
100%	Zero Base Voltage Collector Leakage Current	I_{CES}	--	0.5	mA	$V_{CE} = 50V, V_{BE} = 0V, T_F = 25\pm 5^\circ C.$
100%	DC Current Gain	H_{FE}	20	100	--	$V_{CE} = 5V, I_C = 500mA, T_F = 25\pm 5^\circ C.$

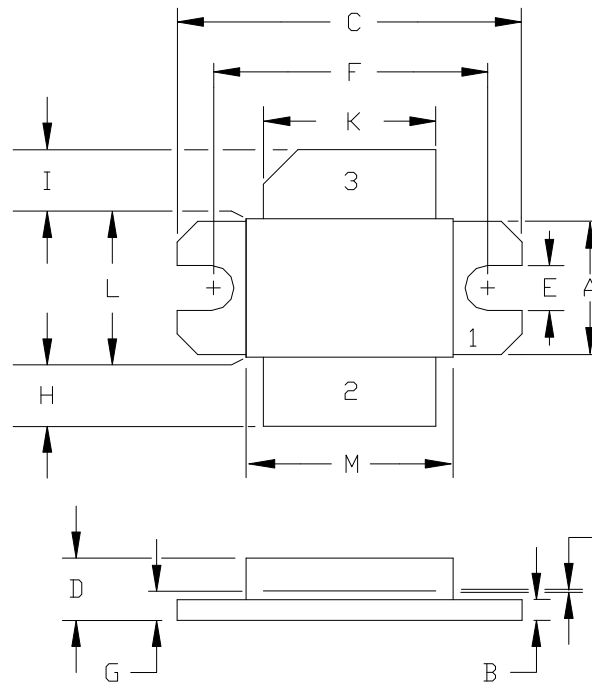
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	10	--	dB	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3
100%	Power Gain	G_P	9	13.0	dB	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3
100%	Collector Efficiency ($P_o/I_c/V_{CC}$)	N_C	50	--	%	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3
100%	Stability into 1.5:1 VSWR	VSWR-S	--	2:1	--	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3 Rotate 2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	Load Mismatch Tolerance	LMT		3:1	--	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3 Rotate 3:1 output VSWR through 360° phase. Survival.
BD	Maximum Input Overdrive	MIO	--	1.0	dB	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3
BD	Pulse Risetime	RT	--	100	ns	$V_{CC}=50V, P_{OUT}=1000W$, Pulse = Note 2, $T_F=30\pm5^\circ C$, F=F1, F2, F3 Measure between 10% and 90% detected power points.
Note 1	F1 = 653MHz, F2 = 670MHz, F3 = 687MHz					
Note 2	Pulse Format : PW=20us, DF=2%					
Note 3	T_F = Device flange temperature.					
Note 4	Screen 'BD' = parameter qualified By Design.					
Note 5	Continuous operation at $V_{CC}=55V$ is allowed only for PW=3us and DF<0.5%					

RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
650	3.13-j0.9	0.72-j0.89
670	3.25-j0.4	0.69-j0.62
690	3.39-j0.1	0.68-j0.35
Impedance Definition		

PACKAGE DIMENSIONAL OUTLINE DRAWING



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.380	0.390	9.65	9.91
B	0.055	0.065	1.40	1.65
C	0.905	1.005	22.99	25.53
D	0.178	0.188	4.52	4.78
E	0.125	0.135	3.18	3.43
F	0.795	0.805	20.19	20.45
G	0.082	0.092	2.08	2.34
H	0.185	0.215	4.70	5.46
I	0.185	0.215	4.70	5.46
J	0.002	0.004	0.05	0.10
K	0.495	0.505	12.57	12.83
L	0.395	0.405	10.03	10.29
M	0.595	0.605	15.11	15.37

PIN SCHEDULE	
1	BASE
2	EMITTER
3	COLLECTOR

Part Number: **IB0607S1000 (Preliminary)**

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RF TEST FIXTURE DRAWING

SEE RF TEST FIXTURE CAD DRAWING

DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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